MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK10A80W

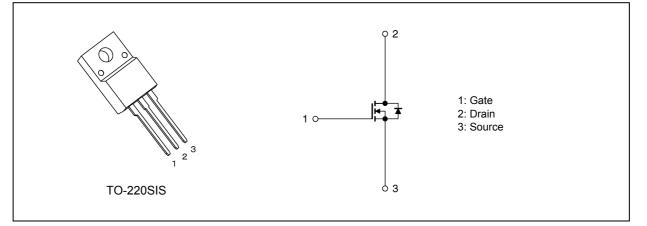
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.46 \Omega$ (typ.) by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 3.0 to 4.0 V (V_{DS} = 10 V, I_D = 0.45mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	800	V
Gate-source voltage		V _{GSS}	±20	1
Drain current (DC)	(Note 1)	Ι _D	9.5	Α
Drain current (pulsed)	(Note 1)	I _{DP}	38	1
Power dissipation (T	_c = 25°C)	PD	40	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	332	mJ
Single-pulse avalanche current		I _{AS}	1.9	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	9.5	1
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	38	1
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	1
Isolation voltage (RMS) (t	= 1.0 s)	V _{ISO(RMS)}	2000	V
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	3.12	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	62.5	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 167 mH, R_G = 25 Ω , I_{AS} = 1.9 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 800 V, V_{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	800	_	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.45 mA	3.0	—	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 4.8 A		0.46	0.55	Ω

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz	_	1150	_	pF
Reverse transfer capacitance	C _{rss}	1	_	2	_	
Output capacitance	C _{oss}		_	27	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 640 V, V_{GS} = 0 V	—	29		
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz	_	35.0	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	35	_	ns
Switching time (turn-on time)	t _{on}	1	_	65	_	
Switching time (fall time)	t _f		_	10	_	
Switching time (turn-off time)	t _{off}	1		120	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \le V_{(BR)DSS}, I_D \le 9.5 A$	50	_		V/ns

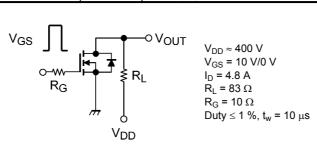


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 640 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 9.5 A		19	—	nC
Gate-source charge 1	Q _{gs1}		_	7	_	
Gate-drain charge	Q _{gd}			6	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 9.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	V _{DD} ≈ 640 V	_	300	_	ns
Reverse recovery charge	Q _{rr}	I _{DR} = 4.8 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs	_	3.2	_	μC
Peak reverse recovery current	l _{rr}		_	22	_	А
Diode dv/dt ruggedness	dv/dt	$V_{DS} \leq 640$ V, $I_{DR} \leq 4.8$ A, V_{GS} = 0 V	4.5			V/ns

7. Marking (Note)

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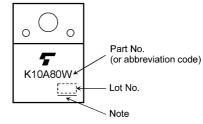


Fig. 7.1 Marking

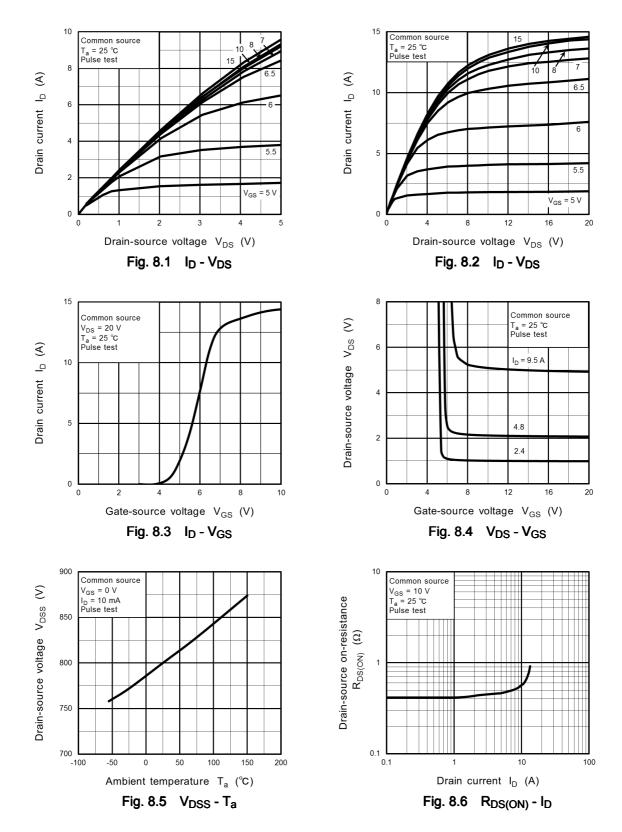
 Note:
 A line under a Lot No. identifies the indication of product Labels.

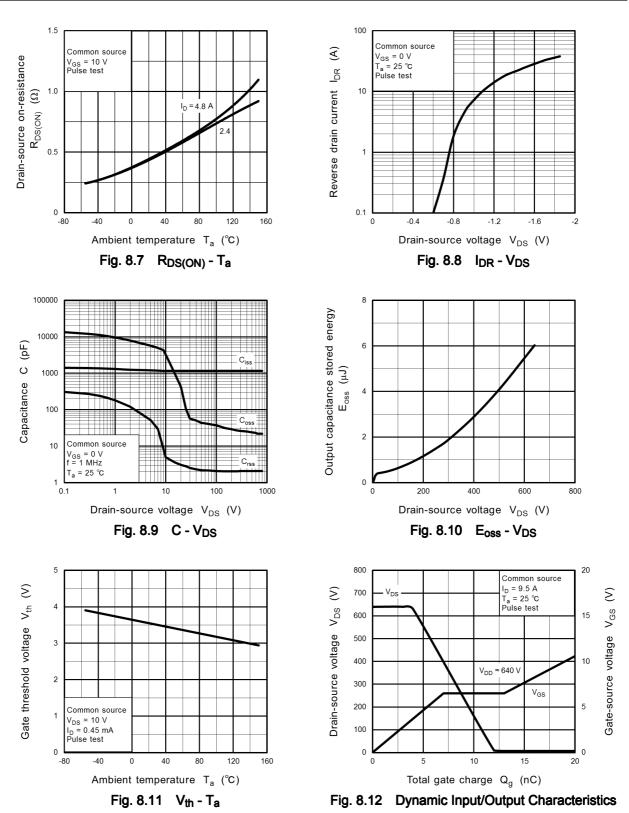
 Not underlined: [[Pb]]/INCLUDES > MCV
 Underlined: [[C]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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 The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)





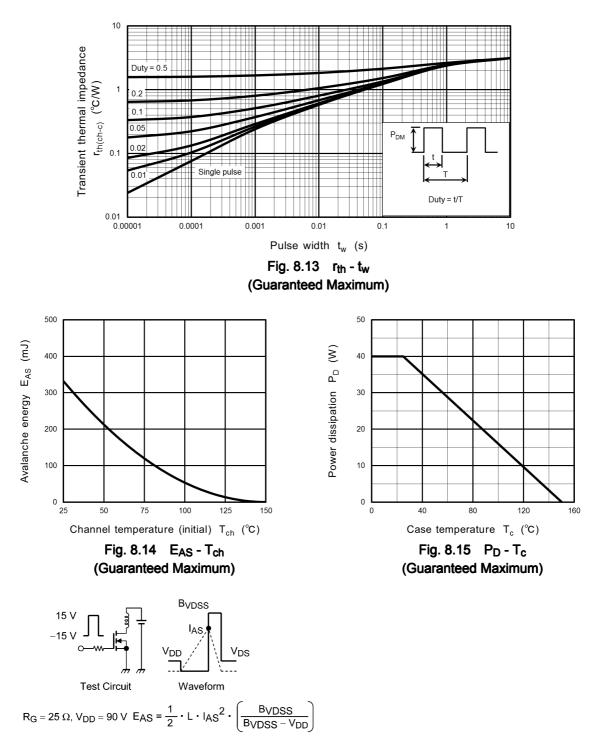
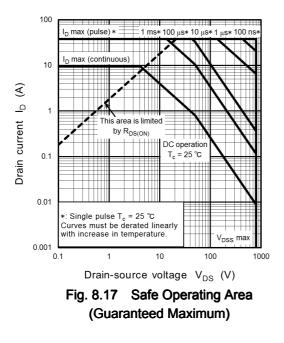


Fig. 8.16 Test Circuit/Waveform

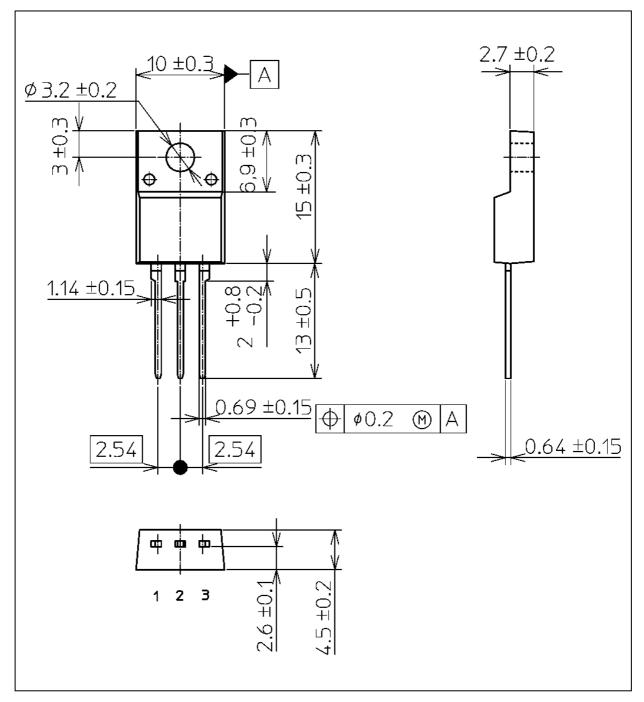


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

TK10A80W

Unit: mm



Weight: 1.7 g (typ.)

	Package Name(s)
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

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